

## LOW FREQUENCY GENERAL PURPOSE AMPLIFIER TRANSISTOR

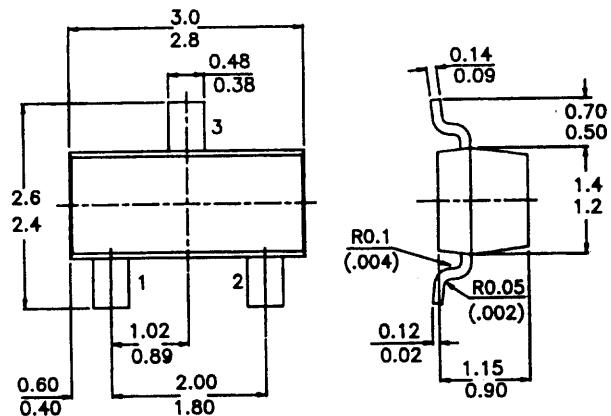
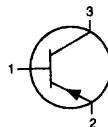
P-N-P transistor

**Marking**

CSA1162Y-3E  
CSA1162GR(G)-3F

**PACKAGE OUTLINE DETAILS**  
**ALL DIMENSIONS IN mm**

**Pin configuration**  
 1 = BASE  
 2 = Emitter  
 3 = COLLECTOR

**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	max.	150 mW
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$
D.C. current gain $-I_C = 2 \text{ mA}; -V_{CE} = 6 \text{ V}$	$h_{FE}$	min.	70
		max.	400

**RATINGS (at  $T_A = 25^\circ\text{C}$  unless otherwise specified)****Limiting values**

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Base current	$-I_B$	max.	30 mA

Total power dissipation at $T_{amb} = 25^\circ C$	$P_{tot}$	max.	150 mW
Storage temperature	$T_{stg}$	-50 to +150	$^\circ C$
Junction temperature	$T_j$	max.	150 $^\circ C$

**CHARACTERISTICS (at  $T_A = 25^\circ C$  unless otherwise specified)****Collector-emitter breakdown voltage** $-I_C = 1 \text{ mA}; I_B = 0$        $-V_{(BR)CEO}$  min      50 V**Collector cut-off current** $-V_{CB} = 50 \text{ V}; I_E = 0$        $-I_{CBO}$  max.      100 nA**Emitter cut-off current** $V_{EB} = 5 \text{ V}; I_C = 0$        $I_{EBO}$  max.      100 nA**Saturation voltage** $-I_C = 100 \text{ mA}; -I_B = 10 \text{ mA}$        $-V_{CEsat}$  max.      0.3 V**D.C. current gain** $I_C = 2 \text{ mA}; -V_{CE} = 6 \text{ V}$        $h_{FE}$  min.      70

max.      400

 $\gamma$  min.      120

max.      240

 $GR(G)$  min.      200

max.      400

**Transition frequency** $V_{CE} = 10 \text{ V}; I_C = 1 \text{ mA}$        $f_T$  min.      80 MHz**Collector output capacitance** $V_{CB} = 10 \text{ V}; I_E = 0; f = 1 \text{ MHz}$        $C_{ob}$  max.      7 pF**Noise figure** $V_{CE} = 6 \text{ V}; I_C = 0.1 \text{ mA}$   
 $f = 1 \text{ kHz}; R_g = 10 \text{ k}\Omega$        $N_F$  max.      10 dB